

In the Claims

Please replace the claims with the following clean version of the entire set of pending claims, in accordance with 37 CFR § 1.121(c)(1)(i). Cancel all previous versions of any pending claim.

A marked-up version showing amendments to any claims being changed is provided in one or more accompanying pages separate from this amendment in accordance with 37 CFR § 1.121(c)(1)(ii). Any claim not accompanied by a marked-up version has not been changed relative to the immediate prior version, except that marked-up versions are not being supplied for any added claim or canceled claim.

CLAIMS

1. (Amended) A chemical vapor deposition method of forming a barium strontium titanate comprising dielectric layer, comprising:

positioning a substrate within a chemical vapor deposition reactor; and

simultaneously a) providing gaseous barium and strontium within the reactor by flowing at least one metal organic precursor to the reactor, b) providing gaseous titanium within the reactor, and c) flowing at least one gaseous oxidizer to the reactor under conditions effective to deposit a barium strontium titanate comprising dielectric layer on the substrate, the oxidizer comprising H₂O.

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2. The method of claim 1 comprising flowing another inorganic oxidizer to the reactor during the deposit.

3. The method of claim 1 wherein the conditions comprise receipt of the substrate by a susceptor, the susceptor having a temperature of less than or equal to 550°C.

4. The method of claim 1 wherein the deposited layer is substantially homogeneous.

5. The method of claim 1 wherein the deposited layer is not substantially homogeneous.

6. (Amended) A chemical vapor deposition method of forming a barium strontium titanate comprising dielectric layer, comprising:
positioning a substrate within a chemical vapor deposition reactor; and
simultaneously a) providing gaseous barium and strontium within the reactor by flowing at least one metal organic precursor to the reactor, and
b) providing gaseous titanium within the reactor, and c) flowing at least one gaseous oxidizer to the reactor under conditions effective to deposit a barium strontium titanate comprising dielectric layer on the substrate, the oxidizer comprising H₂O₂.

7. The method of claim 6 comprising flowing another inorganic oxidizer to the reactor during the deposit.

8. The method of claim 6 wherein the conditions comprise receipt of the substrate by a susceptor, the susceptor having a temperature of less than or equal to 550°C.

9. The method of claim 6 wherein the deposited layer is substantially homogeneous.

10. The method of claim 6 wherein the deposited layer is not substantially homogeneous.

11. (Amended) A chemical vapor deposition method of forming a barium strontium titanate comprising dielectric layer, comprising:

positioning a substrate within a chemical vapor deposition reactor; and

simultaneously a) providing gaseous barium and strontium within the reactor by flowing at least one metal organic precursor to the reactor, and b) providing gaseous titanium within the reactor, and c) flowing gaseous oxidizers to the reactor under conditions effective to deposit a barium strontium titanate comprising dielectric layer on the substrate, the oxidizers comprising at least H_2O and at least another oxidizer selected from the group consisting of O_2 , O_3 , NO_x , N_2O , and H_2O_2 , where "x" is at least 1.

12. The method of claim 11 wherein the another oxidizer comprises O_2 .

13. The method of claim 11 wherein the another oxidizer comprises O_3 .

14. The method of claim 11 wherein the another oxidizer comprises NO_x , where "x" is at least 1.

15. The method of claim 11 wherein the another oxidizer comprises N_2O .

16. The method of claim 11 wherein the another oxidizer comprises H_2O_2 .

17. The method of claim 11 the oxidizers comprise at least two of the another oxidizers.

18. (Amended) A chemical vapor deposition method of forming a barium strontium titanate comprising dielectric layer, comprising:
positioning a substrate within a chemical vapor deposition reactor; and
simultaneously a) providing gaseous barium and strontium within the reactor by flowing at least one metal organic precursor to the reactor, b) providing gaseous titanium within the reactor, and c) flowing gaseous oxidizers to the reactor under conditions effective to deposit a barium strontium titanate comprising dielectric layer on the substrate, the oxidizers comprising at least H_2O_2 and at least another oxidizer selected from the group consisting of O_2 , O_3 , NO_x , and N_2O , where "x" is at least 1.

19. The method of claim 18 wherein the another oxidizer comprises O_2 .

20. The method of claim 18 wherein the another oxidizer comprises O_3 .

21. The method of claim 18 wherein the another oxidizer comprises NO_x , where "x" is at least 1.

22. The method of claim 18 wherein the another oxidizer comprises N_2O .

23. The method of claim 18 wherein the another oxidizer comprises H_2O_2 .

24. The method of claim 18 the oxidizers comprise at least two of the another oxidizers.